10-E1126TA035M7-L859F73Z
datasheet

***flow*PACK E1** **1200 V / 35 A**

Topology features

- Inverter
- Kelvin Emitter for improved switching performance
- Tandem inverter diode
- Temperature sensor

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current
- Switching optimized for EMC

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Solder pin

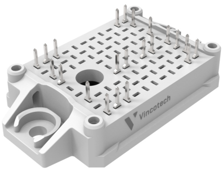
Target applications

- Elevator Drives
- Industrial Drives
- Servo Drives

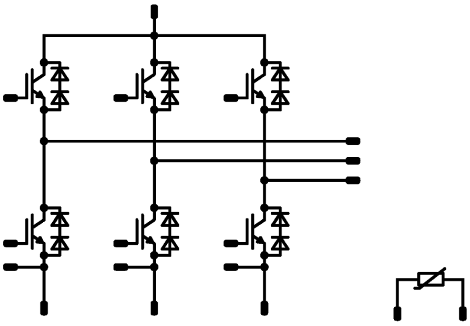
Types

- 10-E1126TA035M7-L859F73Z

flow E1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ T_s = 80 °C	51	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	70	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	109	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V T_j = 150 °C	9,5	µs
Maximum junction temperature	T_{jmax}		175	°C
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1300	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	86	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			8,62	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_{F} [V]	I_{C} [A] I_{D} [A] I_{F} [A]	T_{j} [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0035	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		35	25 125 150		1,47 1,64 1,68	1,85(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			80	µA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_{g}							None		Ω
Input capacitance	C_{ies}		0	10		25		7900		pF
Output capacitance	C_{oes}							270		pF
Reverse transfer capacitance	C_{res}							97		pF
Gate charge	Q_{g}	V_{CC} = 600 V	0/15		35	25		260		nC
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 5,2 W/mK (PTM)						0,87		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	600	35	25 125 150		71,98 72,1 72,05		ns
Rise time	t_{r}					25 125 150		16,84 18,76 19,3		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		146,93 175,04 183,49		ns
Fall time	t_{f}					25 125 150		89,92 126,04 133,2		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,735 µC Q_{rFWD}=1,5 µC Q_{rFWD}=1,74 µC				25 125 150		1,1 1,6 1,73		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		2,47 3,46 3,66		mWs

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_F **[V]**	I_C **[A]** I_D **[A]** I_F **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Inverter Diode										
Static										
Forward voltage	V_F				30	25 125 150		3,19 3,01 2,93	3,84(1)	V
Reverse leakage current	I_R	V_r = 1300 V				25			1,6	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 5,2 W/mK (PTM)						1,1		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=1163 A/µs d*i*/d*t*=1353 A/µs d*i*/d*t*=1196 A/µs	±15	600	35	25 125 150		15,95 22,45 23,91		A
Reverse recovery time	t_{rr}					25 125 150		86,47 123,49 139,73		ns
Recovered charge	Q_r					25 125 150		0,735 1,5 1,74		µC
Reverse recovered energy	E_{rec}					25 125 150		0,249 0,53 0,622		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		233,66 239,22 229,04		A/µs

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_F **[V]**	I_C **[A]** I_D **[A]** I_F **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

(1) Value at chip level

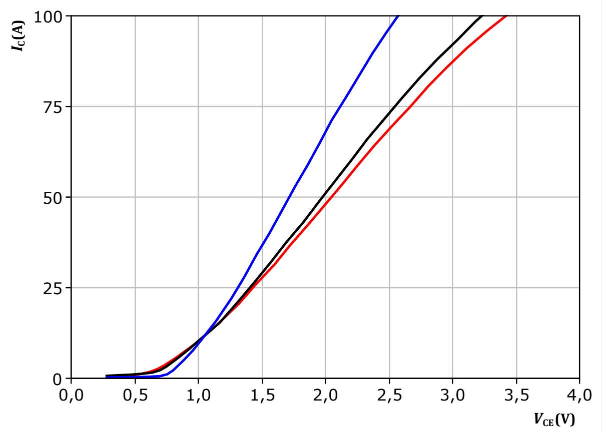
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 µs

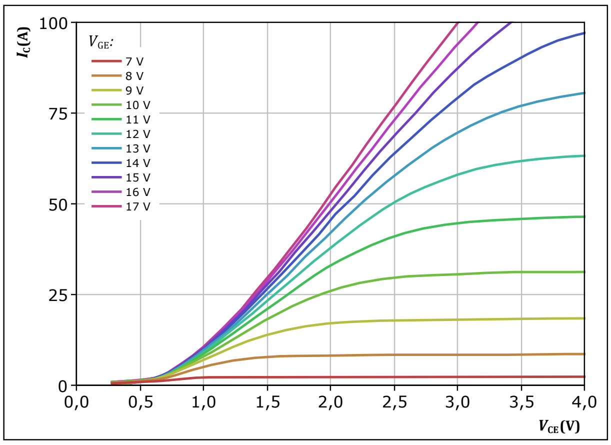
V_{GE} = 15 V

T_j: 25 °C, 125 °C, 150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 µs

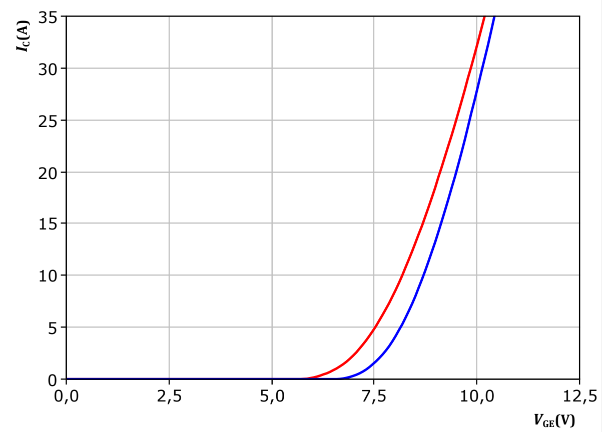
T_j = 150 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



t_p = 250 µs

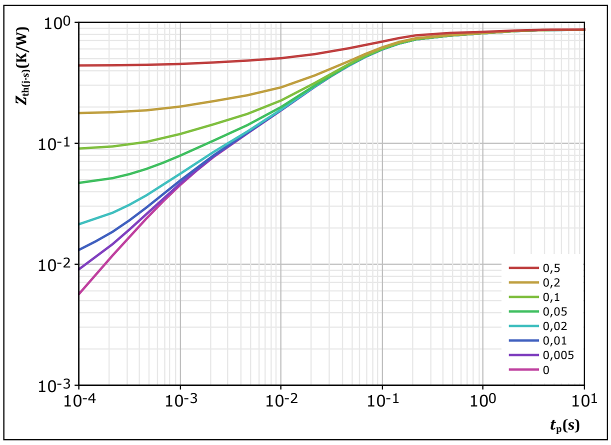
V_{CE} = 10 V

T_j: 25 °C, 125 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,872 K/W

IGBT thermal model values

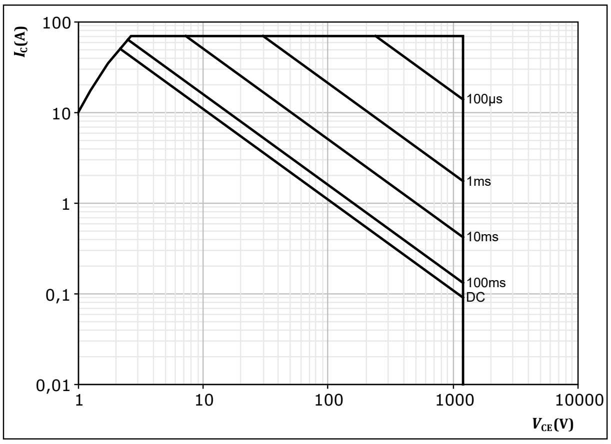
R (K/W)	τ (s)
1,33E-02	1,77E+01
1,36E-01	1,01E+00
5,35E-01	7,55E-02
1,38E-01	1,54E-02
5,39E-02	1,28E-03

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

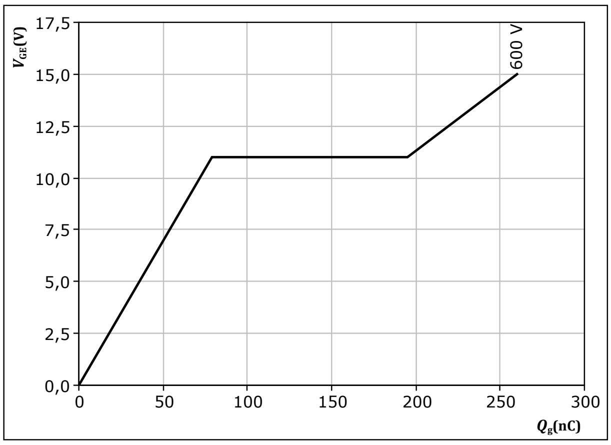


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



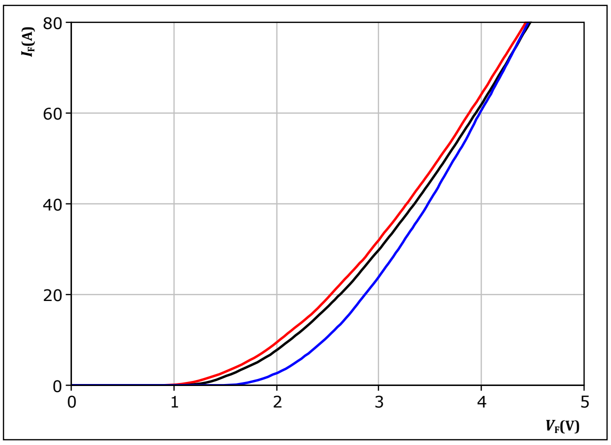
I_C = 35 A
T_j = 25 °C

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

I_F = f(V_F)



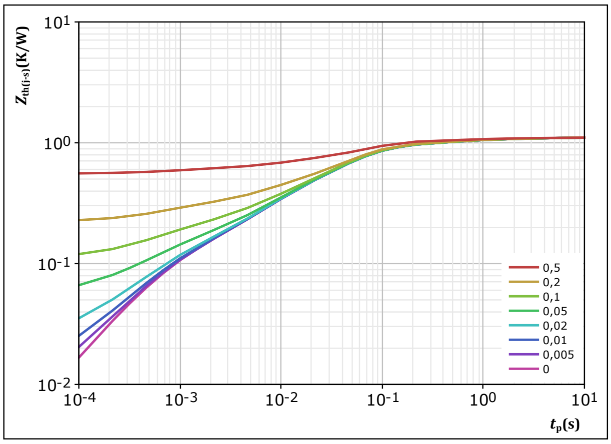
t_p = 250 µs

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,104 K/W

FWD thermal model values

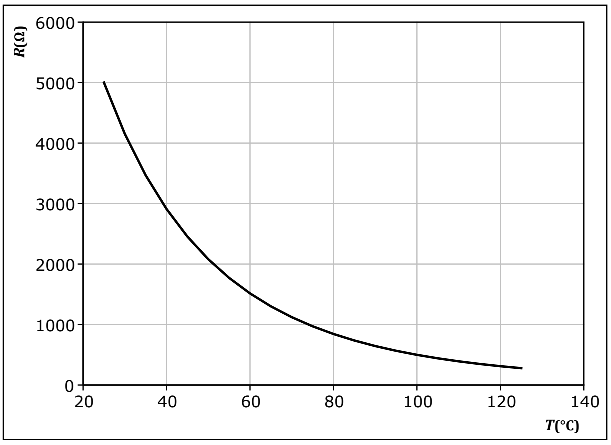
R (K/W)	τ (s)
4,66E-02	4,05E+00
1,39E-01	4,71E-01
6,58E-01	5,02E-02
1,75E-01	7,05E-03
8,87E-02	6,38E-04

Thermistor Characteristics

figure 9. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

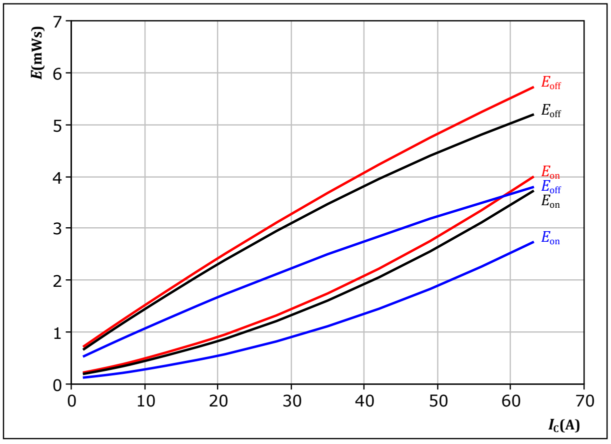


Inverter Switching Characteristics

figure 10. **IGBT**

Typical switching energy losses as a function of collector current

$E = \mathrm{f}(I_C)$



With an inductive load at

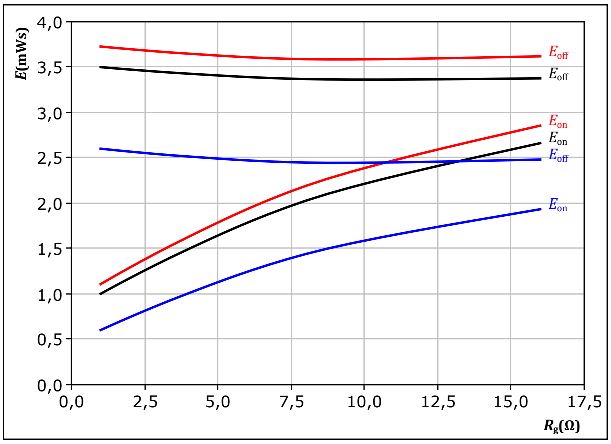
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω
R_{goff} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 11. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = \mathrm{f}(R_g)$



With an inductive load at

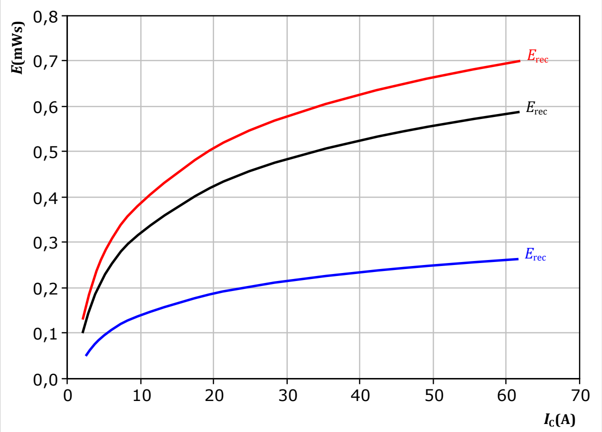
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

T_j:
25 °C
125 °C
150 °C

figure 12. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = \mathrm{f}(I_C)$



With an inductive load at

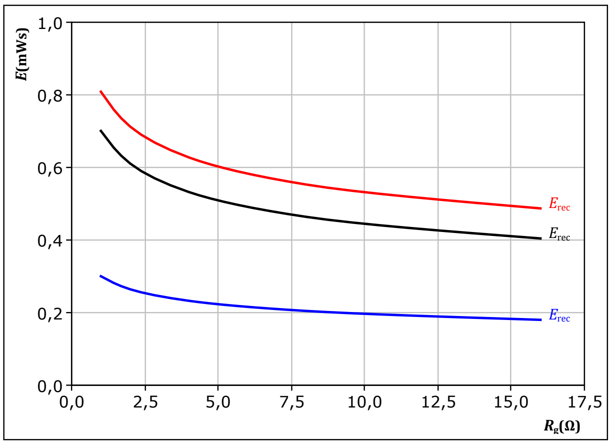
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = \mathrm{f}(R_g)$



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

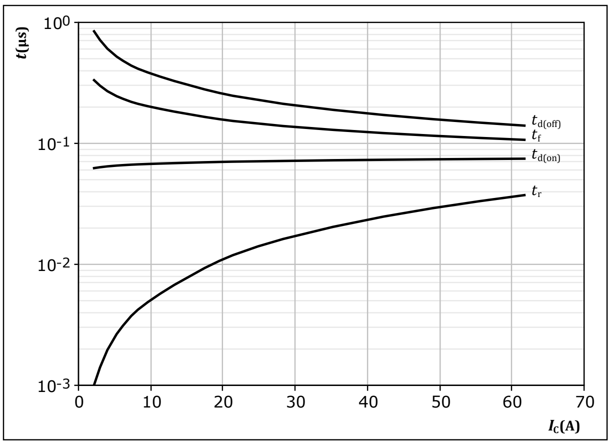
T_j:
25 °C
125 °C
150 °C

Inverter Switching Characteristics

figure 14. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



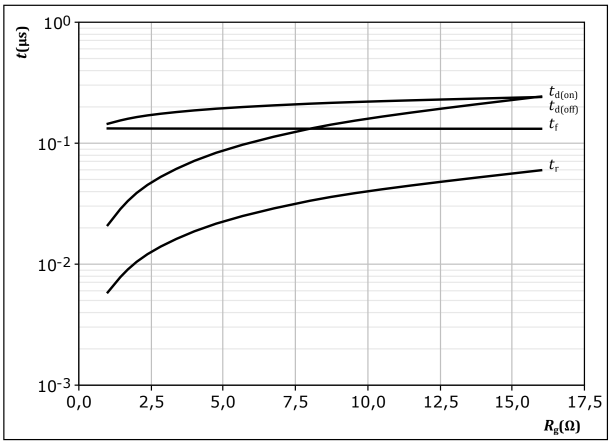
With an inductive load at

T_j = 150 °C
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω
R_{goff} = 4 Ω

figure 15. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



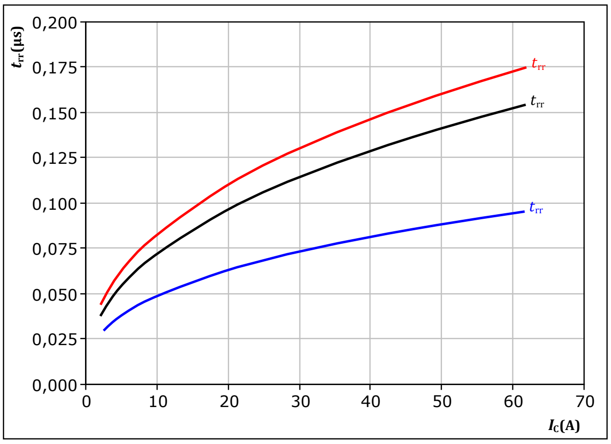
With an inductive load at

T_j = 150 °C
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

figure 16. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

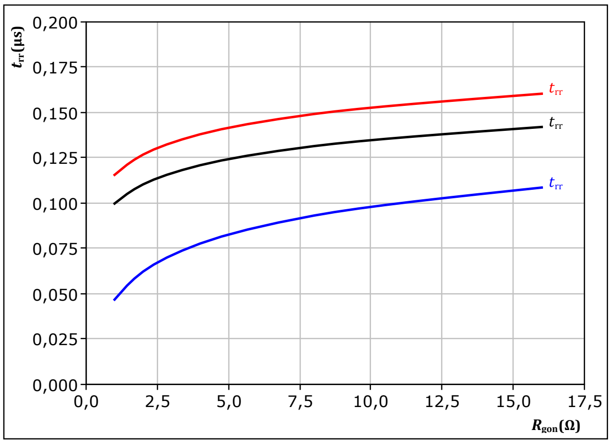
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
25 °C
125 °C
150 °C

figure 17. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

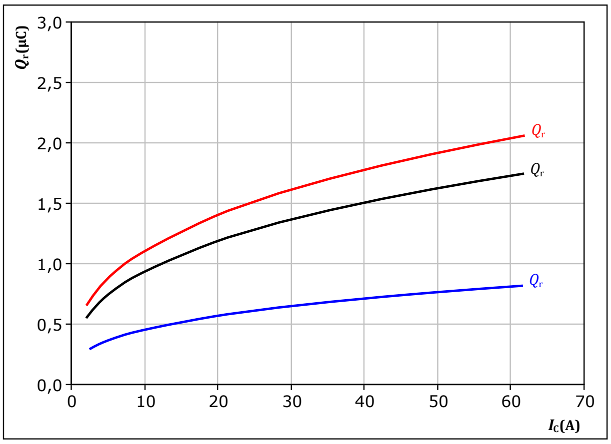
T_j:
25 °C
125 °C
150 °C

Inverter Switching Characteristics

figure 18. FWD

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

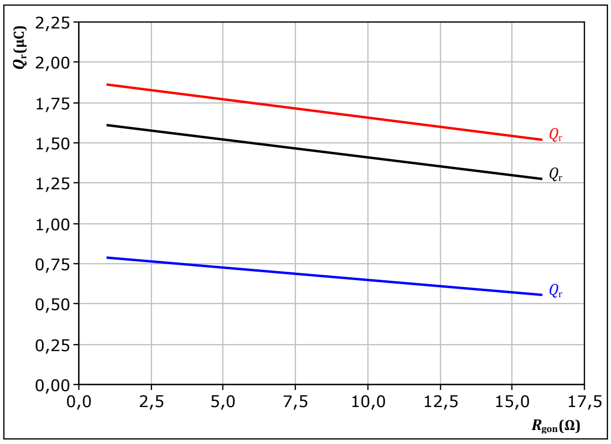
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 19. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

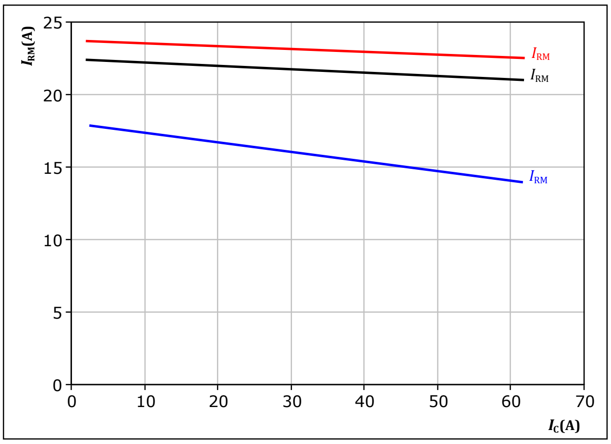
V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 20. FWD

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

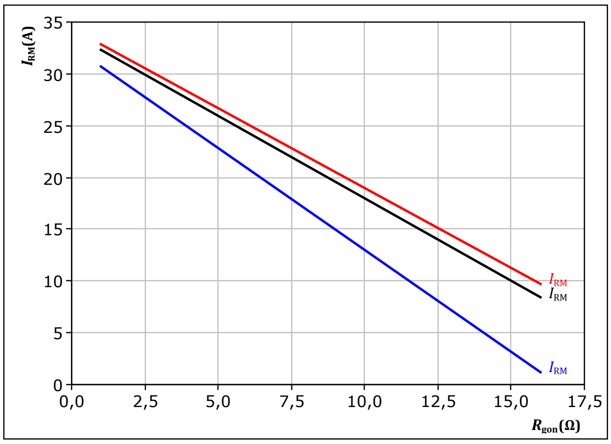
V_{CE} = 600 V
V_{GE} = ±15 V
R_{gon} = 4 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 21. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

V_{CE} = 600 V
V_{GE} = ±15 V
I_C = 35 A

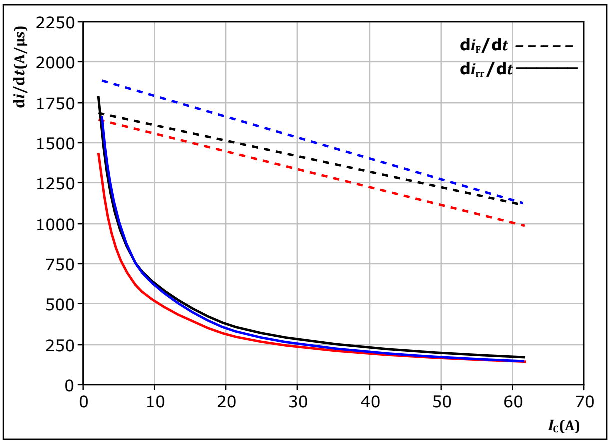
T_j:
— 25 °C
— 125 °C
— 150 °C

Inverter Switching Characteristics

figure 22. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



With an inductive load at

V_{CE} = 600 V

V_{GE} = ±15 V

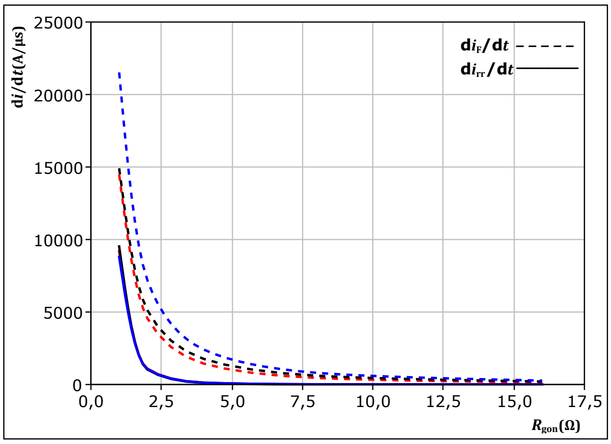
R_{gon} = 4 Ω

T_j: 25 °C / 125 °C / 150 °C

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



With an inductive load at

V_{CE} = 600 V

V_{GE} = ±15 V

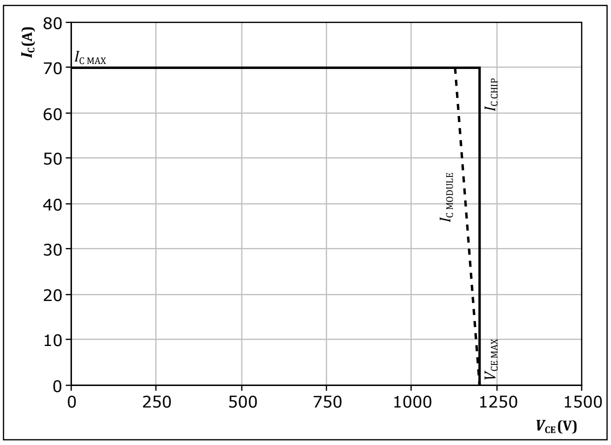
I_C = 35 A

T_j: 25 °C / 125 °C / 150 °C

figure 24. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At T_j = 150 °C

R_{gon} = 4 Ω

R_{goff} = 4 Ω

Inverter Switching Definitions

figure 25. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} **(**t_{tEoff} **= integrating time for** E_{off}**)**

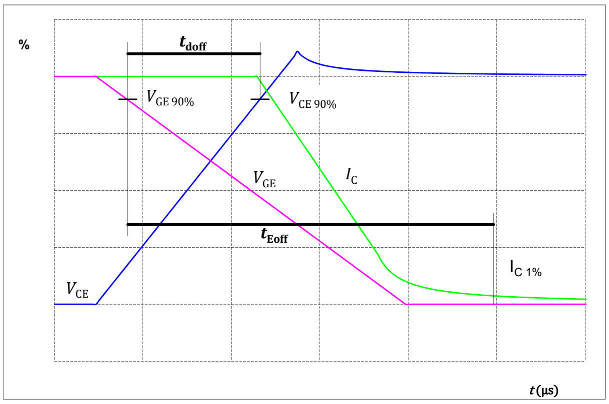


figure 26. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} **(**t_{Eon} **= integrating time for** E_{on}**)**

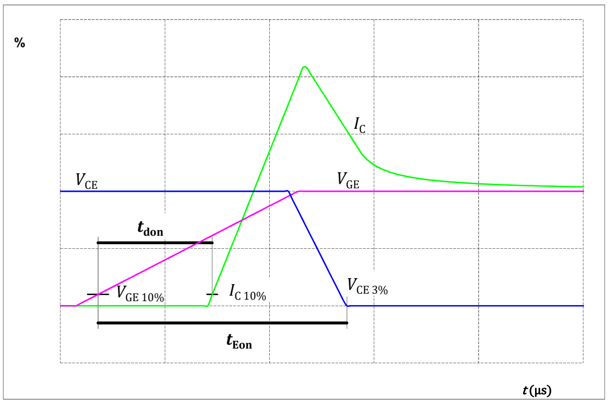


figure 27. **IGBT**

Turn-off Switching Waveforms & definition of t_f

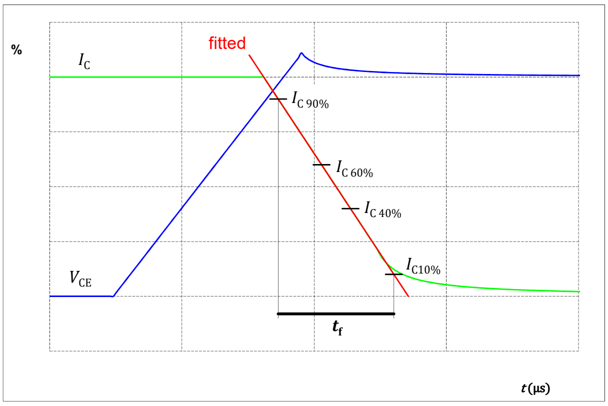
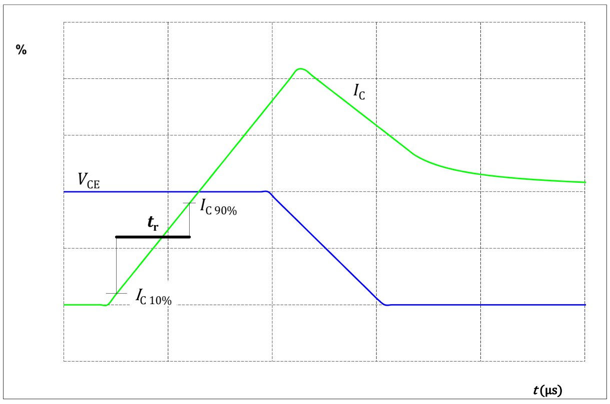


figure 28. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 29. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

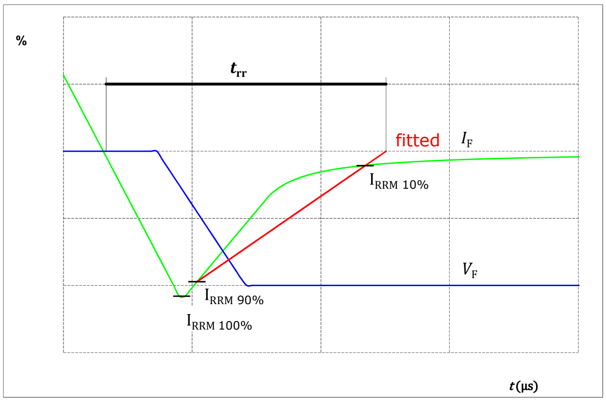
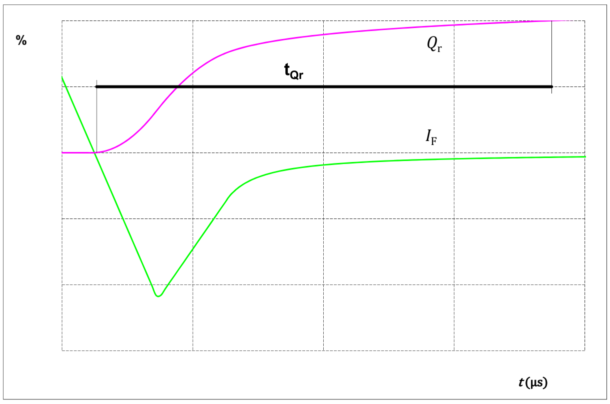


figure 30. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

Version	Ordering Code
Without thermal paste	10-E1126TA035M7-L859F73Z
With thermal paste (5,2 W/mK, PTM6000HV)	10-E1126TA035M7-L859F73Z-/7/

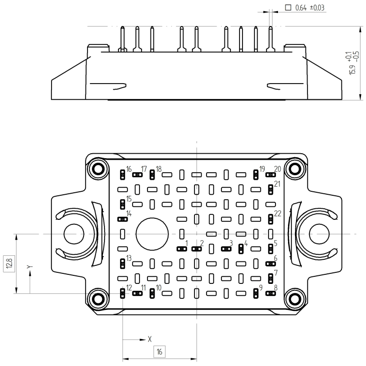
Marking

		**Name**		**Date code**	**UL & VIN**	**Lot**	**Serial**
	Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

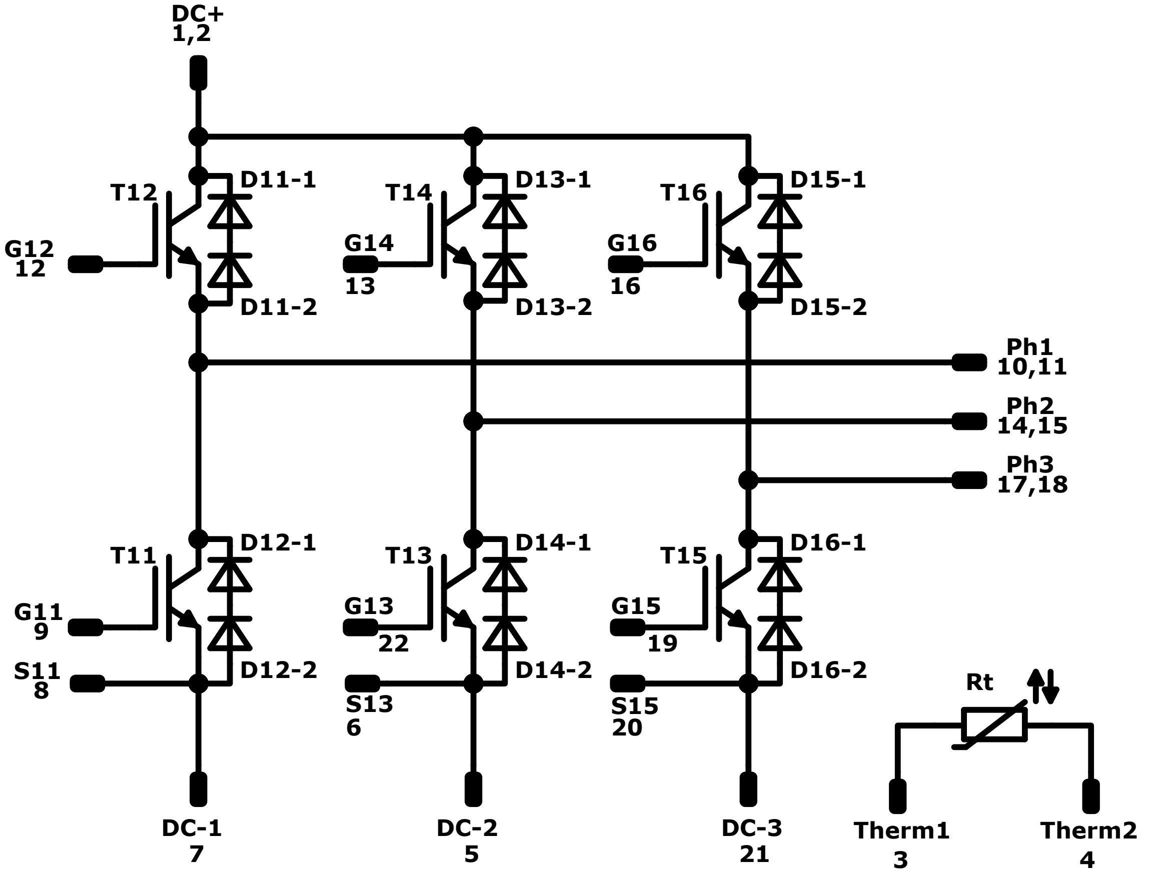
Pin table [mm]

Pin	X	Y	Function
1	12,8	9,6	DC+
2	16	9,6	DC+
3	22,4	9,6	Therm1
4	25,6	9,6	Therm2
5	32	9,6	DC-2
6	32	6,4	S13
7	32	3,2	DC-1
8	32	0	S11
9	28,8	0	G11
10	6,4	0	Ph1
11	3,2	0	Ph1
12	0	0	G12
13	0	6,4	G14
14	0	16	Ph2
15	0	19,2	Ph2
16	0	25,6	G16
17	3,2	25,6	Ph3
18	6,4	25,6	Ph3
19	28,8	25,6	G15
20	32	25,6	S15
21	32	22,4	DC-3
22	32	16	G13



Tolerance of pinpositions: ±0.4mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	35 A	Inverter Switch	
D11-1, D11-2, D12-1, D12-2, D13-1, D13-2, D14-1, D14-2, D15-1, D15-2, D16-1, D16-2	FWD	1300 V	30 A	Inverter Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	**Date:**	**Modification:**	**Pages**
10-E1126TA035M7-L859F73Z-D1-14	22 Aug. 2025	Initial Release	

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